

IN THE CLAIMS

Please amend the claims to read as follows:

1. (Original) A method for manufacturing a high voltage device and a low voltage device comprising steps of:
 - (a) depositing a first oxidation film and a nitride film sequentially on a SOI substrate where a lower substrate, a buried oxidation film and an upper silicon layer are sequentially stacked;
 - (b) removing the nitride film and the first oxidation film of the high voltage device region by etching, after defining the high voltage device region on a total structure;
 - (c) forming the upper silicon layer of the high voltage device region thinner than the upper silicon layer of the low voltage device region by growing a second oxidation film in the high voltage device region;
 - (d) removing the second oxidation film and the remaining portions of the nitride film and the first oxidation film;
 - (e) forming the high voltage device region and the low voltage device region by etching the upper silicon layer, after defining a device isolation region;
 - (f) forming a p-well in the low voltage device region, and a p-well and a drift region in the high voltage device region;
 - (g) forming a thin gate insulation film in the low voltage device region, and a thick gate insulation film in the high voltage device region;
 - (h) forming a gate electrode, a LDD region, a sidewall oxidation film, a source region and a drain region in the low voltage device region and the high voltage device region, respectively; and
 - (i) forming a source electrode and a drain electrode, after depositing an interlayer insulation film on an upper surface of a total structure.

2. (Original) The method as claimed in claim 1, wherein in the (c) step, the second oxidation film is grown to have 6000~8000 Å in thickness, and

the upper silicon layer of the high voltage device region is in a range of 0.2~0.5 μm in thickness.

3. (Original) The method as claimed in claim 1,
wherein in the (c) step,
the second oxidation film is grown by using a high-pressure oxidation growth process.

4. (Original) The method as claimed in claim 1,
wherein the (g) step comprises steps of;
forming a third oxidation film in the high voltage device region and the low voltage device region;
performing ion implantation in the low voltage device region, thereby a threshold voltage being adjustable;
removing the third oxidation film formed in the low voltage device region; and
forming a fourth oxidation film on the high voltage device region and the low voltage device region.

5. (Currently Amended) The method as claimed in claim 1,
wherein in the (h) step,
a thickness of the silicon device region, where the high voltage device is formed, is ~~intended to be~~ equal to a junction depth of impurities of the source and drain in the low voltage device.

6 – 13 (Canceled)